



SIHP12N60E-GE3 Information



For Reference Only

Part Number SIHP12N60E-GE3
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 600V 12A TO220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SIHP12N60E-GE3 Specifications

Manufacturer Part Number SIHP12N60E-GE3 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series E FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 12A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 58nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 937pF @ 100V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 147W (Tc) Rds On (Max) @ Id, Vgs 380 mOhm @ 6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series E FET Type N-Channel Technology MOSFET (Metal Oxide) To voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 12A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Rds On (Max) @ Id, Vgs Rds On (Max) @ Id, Vgs Through Hole Supplier Device Package Package / Case Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single TO-220AB Package / Case	Manufacturer Part Number	SIHP12N60E-GE3
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C12A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs58nC @ 10VInput Capacitance (Ciss) (Max) @ Vds937pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)147W (Tc)Rds On (Max) @ Id, Vgs380 mOhm @ 6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C12A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs58nC @ 10VInput Capacitance (Ciss) (Max) @ Vds937pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)147W (Tc)Rds On (Max) @ Id, Vgs380 mOhm @ 6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Series	E
Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C12A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs58nC @ 10VInput Capacitance (Ciss) (Max) @ Vds937pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)147W (Tc)Rds On (Max) @ Id, Vgs380 mOhm @ 6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C12A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs58nC @ 10VInput Capacitance (Ciss) (Max) @ Vds937pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)147W (Tc)Rds On (Max) @ Id, Vgs380 mOhm @ 6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs58nC @ 10VInput Capacitance (Ciss) (Max) @ Vds937pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)147W (Tc)Rds On (Max) @ Id, Vgs380 mOhm @ 6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Drain to Source Voltage (Vdss)	600V
Vgs(th) (Max) @ Id	Current - Continuous Drain (Id) @ 25°C	12A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 937pF @ 100V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 380 mOhm @ 6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)147W (Tc)Rds On (Max) @ Id, Vgs380 mOhm @ 6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	58nC @ 10V
FET Feature - 147W (Tc) Rds On (Max) @ Id, Vgs 380 mOhm @ 6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	937pF @ 100V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 380 mOhm @ 6A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs380 mOhm @ 6A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Power Dissipation (Max)	147W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	380 mOhm @ 6A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

SIHP12N60E-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SIHP12N60E-GE3 Payment Methods



















SIHP12N60E-GE3 Shipping Methods













If you have any question about SIHP12N60E-GE3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com